

Takashi Hanada

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Temperature Characteristics of Resonance Frequency for Double-Layered Thickness-Shear Resonator. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2022, 69, 870-877.	3.0	3
2	Growth of Tb-doped BaCl ₂ /NaCl/KCl ternary eutectic and its luminescence properties. Journal of Crystal Growth, 2022, 580, 126467.	1.5	3
3	Growth of Ce-doped LiBr/LaBr_6 ternary eutectic and its luminescence properties. Journal of Crystal Growth, 2022, 580, 126467.	1.6	8
4	Crystal growth of La ₂ Hf ₂ O ₇ by micro-pulling-down method using W crucible. Journal of Crystal Growth, 2022, 583, 126547.	1.5	6
5	Growth and scintillation properties of directionally solidified Ce:LaCl ₃ /AeCl ₂ (Ae = Mg, Ca, Sr) eutectic Scintillators. Journal of Crystal Growth, 2022, 584, 126549.	1.5	1
6	Open-source simulator of total-reflection high-energy positron diffraction (TRHEPD) and reflection high-energy electron diffraction (RHEED). Computer Physics Communications, 2022, 277, 108371.	7.5	5
7	Crystal growth of La ₂ Zr ₂ O ₇ by micro-pulling-down method using Mo and W crucibles. Journal of Crystal Growth, 2021, 575, 126357.	1.5	2
8	Growth and scintillation properties of Tl-doped CsI/KI/KCl ternary eutectics. Journal of Crystal Growth, 2021, 573, 126287.	1.5	3
9	Growth and scintillation properties of Tl-doped CsI/CsCl/NaCl ternary eutectic scintillators. Japanese Journal of Applied Physics, 2021, 60, SBBK01.	1.5	8
10	Dependence of the V/III Ratio on Indium Incorporation in InGaN Films Grown by Metalorganic Vapour Phase Epitaxy. Journal of Nanoscience and Nanotechnology, 2020, 20, 2979-2986.	0.9	4
11	Crystal growth and scintillation properties of tube shape-controlled Ce-doped Y ₃ Al ₅ O ₁₂ single crystals grown by micro-pulling-down method. Applied Physics Express, 2020, 13, 125503.	2.4	5
12	Development of Data-Analysis Software for Total-Reflection High-Energy Positron Diffraction (TRHEPD). Acta Physica Polonica A, 2020, 137, 188-192.	0.5	7
13	Thermodynamic model for metalorganic vapor-phase epitaxy of N-polar group-III nitrides in step-flow growth mode: Hydrogen, competitive adsorption, and configuration entropy. Physical Review Materials, 2019, 3, .	2.4	4
14	Characterization of the ScAlMgO ₄ cleaving layer by X-ray crystal truncation rod scattering. Journal of Applied Physics, 2018, 123, .	2.5	13
15	Ga-polar GaN film grown by MOVPE on cleaved ScAlMgO ₄ (0001) substrate with millimeter-scale wide terraces. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600754.	1.8	21
16	Polarity control of GaN grown on pulsed-laser-deposited AlN/GaN template by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2016, 55, 05FA04.	1.5	5
17	Homogeneity improvement of N-polar InGaN/GaN multiple quantum wells by using c-plane sapphire substrate with off-cut-angle towards a-sapphire plane. Japanese Journal of Applied Physics, 2016, 55, 05FA09.	1.5	13
18	Suppression of metastable-phase inclusion in N-polar (0001) InGaN/GaN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2015, 106, .	3.3	6

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19	Red to blue wavelength emission of N-polar $(000\bar{1})$ InGaN light-emitting diodes grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2015, 8, 061005.	2.4	49
20	Enhancement of surface migration by Mg doping in the metalorganic vapor phase epitaxy of N-polar GaN/sapphire. Japanese Journal of Applied Physics, 2014, 53, 05FL05.	1.5	16
21	Effect of c -plane sapphire substrate miscut angle on indium content of MOVPE-grown N-polar InGaN. Japanese Journal of Applied Physics, 2014, 53, 05FL07.	1.5	7
22	Improvement of surface morphology of nitrogen-polar GaN by introducing indium surfactant during MOVPE growth. Japanese Journal of Applied Physics, 2014, 53, 085501.	1.5	22
23	Effect of Sapphire Nitridation and Group-III Source Flow Rate Ratio on In-Incorporation Into InGaN Grown by Metalorganic Vapor Phase Epitaxy. Journal of Nanoscience and Nanotechnology, 2014, 14, 6112-6115.	0.9	0
24	Investigation of indium incorporation into InGaN by nitridation of sapphire substrate in MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 417-420.	0.8	3
25	Effect of Nitridation on Indium-Composition of InGaN Films. Key Engineering Materials, 2012, 508, 193-198.	0.4	0
26	Tilted Domain and Indium Content of InGaN Layer on m -Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	1.5	3
27	Phase diagram on phase purity of InN grown pressurized μ -reactor MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 654-657.	0.8	10
28	Tilted Domain and Indium Content of InGaN Layer on m -Plane GaN Substrate Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 04DH01.	1.5	3
29	Strain relaxation mechanism of InGaN thin film grown on m -GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 444-446.	0.8	12
30	Electrochemical isothermal-capacitance-transient spectroscopy: A new depth profiling method of deep levels. Review of Scientific Instruments, 2011, 82, 093905.	1.3	0
31	An empirical equation including the strain effect for optical transition energy of strained and fully relaxed GaN films. Journal Physics D: Applied Physics, 2010, 43, 175101.	2.8	4
32	Effect of anion-to-cation supplying ratio on the surface morphology of AlN films grown on ZnO substrates at low temperature. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 61-64.	2.1	0
33	Lattice strain in bulk GaN epilayers grown on CrN/sapphire template. Applied Physics Letters, 2009, 94, 082105.	3.3	41
34	X-ray photoelectron spectroscopy study on the CrN surface grown on sapphire substrate to control the polarity of ZnO by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2009, 255, 8582-8586.	6.1	9
35	The effect of hydrogen irradiation and annealing on the low-temperature growth of homoepitaxial ZnO layers grown on (0001) ZnO substrates by plasma-assisted molecular beam epitaxy. Applied Surface Science, 2008, 254, 3120-3124.	6.1	3
36	Growth of Polarity-Controlled ZnO Films on (0001) Al ₂ O ₃ . Journal of Electronic Materials, 2008, 37, 736-742.	2.2	14

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37	Study of local segregation in GaInNAs using EXAFS measurements. Journal of Physics and Chemistry of Solids, 2008, 69, 298-301.	4.0	1
38	The high quality ZnO growth on c-Al ₂ O ₃ substrate with Cr ₂ O ₃ buffer layer using plasma-assisted molecular beam epitaxy. Applied Surface Science, 2008, 254, 7786-7789.	6.1	10
39	Effects of interfacial layer structures on crystal structural properties of ZnO films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 90-96.	2.1	26
40	Comparative study of photoluminescences for Zn-polar and O-polar faces of single-crystalline ZnO bulks. Applied Physics Letters, 2008, 93, .	3.3	32
41	Optical properties and electrical properties of heavily Al-doped ZnSe layers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 259-264.	2.1	1
42	Strain-free GaN thick films grown on single crystalline ZnO buffer layer with in situ lift-off technique. Applied Physics Letters, 2007, 90, 061907.	3.3	22
43	Impact of V/III ratio on electrical properties of GaN thick films grown by hydride vapor-phase epitaxy. Applied Physics Letters, 2007, 91, .	3.3	25
44	Crystal Growth. , 2007, , 329-445.		1
45	Polarity control of ZnO films on (0001) Al ₂ O ₃ by Cr-compound intermediate layers. Applied Physics Letters, 2007, 90, 201907.	3.3	45
46	Structural investigation of nitrided c-sapphire substrate by grazing incidence x-ray diffraction and transmission electron microscopy. Applied Physics Letters, 2007, 91, 202116.	3.3	7
47	Molecular beam epitaxy and magnetic properties of GaMnNAs. Journal of Crystal Growth, 2007, 301-302, 642-646.	1.5	4
48	Analysis of the relation between leakage current and dislocations in GaN-based light-emitting devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 37-40.	0.8	6
49	Structural characterization of MgO/c-Al ₂ O ₃ interfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1715-1718.	0.8	1
50	Characterization of free-standing GaN substrates prepared by self lift-off. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2617-2620.	0.8	1
51	Metal catalyst enhanced growth of high quality and density GaN dots on Si(111) by implant source growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2314-2317.	0.8	1
52	Lattice relaxation mechanism of ZnO thin films grown on c-Al ₂ O ₃ substrates by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2007, 91, .	3.3	50
53	Low-Temperature Growth of AlN thin films on ZnO templates prepared on Al ₂ O ₃ /SiO ₂ /Si substrates. , 2006, , .		0
54	Magnetic and Crystalline properties of GaMnNAs and Low-temperature annealing effect. , 2006, , .		0

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55	Origin of forward leakage current in GaN-based light-emitting devices. Applied Physics Letters, 2006, 89, 132117.	3.3	148
56	Slowdown in development of self-assembled InAs ^x GaAs(001) dots near the critical thickness. Journal of Vacuum Science & Technology B, 2006, 24, 1886.	1.3	3
57	Correlation between ZnO Nanowire Growth and the Surface of AlN Substrate. Crystal Growth and Design, 2006, 6, 2640-2642.	3.0	4
58	Ordering of In and Ga in Epitaxially Grown In _{0.53} Ga _{0.47} As Films on (001) InP Substrates. Materials Transactions, 2006, 47, 1115-1120.	1.2	2
59	Electrical properties of ZnO/GaN heterostructures and photoresponsivity of ZnO layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 946-951.	0.8	15
60	Observation of a filled electronic state in the conduction band of InN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1846-1849.	0.8	7
61	Photoresponsivity of ZnO Schottky barrier diodes. Journal of Vacuum Science & Technology B, 2006, 24, 1595.	1.3	16
62	Formation and evolution of strain-induced self-assembled dot. Microelectronics Journal, 2005, 36, 216-218.	2.0	4
63	GaN nanodot fabrication by implant source growth. Microelectronics Journal, 2005, 36, 456-459.	2.0	3
64	Soft X-ray spectroscopy of diluted magnetic semiconductor Ga _{1-x} M _x N (M = Cr, Mn). Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 707-710.	1.7	3
65	Electronic structure of the Ga _{1-x} Cr _x N studied by high-energy photoemission spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2005, 144-147, 561-564.	1.7	2
66	GaNAs(001) surface phases under growing condition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1341.	1.6	0
67	Electron-trap centers in ZnO layers grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 032909.	3.3	45
68	Characteristics of Schottky contacts to ZnO:N layers grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 042110.	3.3	39
69	Electrical characterization for ZnO layers grown on GaN templates by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1281.	1.6	4
70	Experimental demonstration of Fano-type resonance in photoluminescence of ZnS:Mn ²⁺ ·SiO ₂ one-dimensional photonic crystals. Applied Physics Letters, 2005, 87, 171106.	3.3	8
71	Structure and magnetic properties of Cr-doped GaN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1308.	1.6	25
72	Novel Method for Site-Controlled Surface Nanodot Fabrication by Ion Beam Synthesis. Nano Letters, 2005, 5, 771-776.	9.1	23

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73	Structural variation of cubic and hexagonal $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ layers grown on $\text{MgO}(111)$ -c-sapphire. <i>Journal of Applied Physics</i> , 2005, 98, 054911.	2.5	107
74	Capacitance-voltage characteristics of ZnO/GaN heterostructures. <i>Applied Physics Letters</i> , 2005, 87, 162104.	3.3	23
75	Hybridization of $\text{Cr}3d$ and $\text{N}2p$ in $\text{Ga}_{1-x}\text{Cr}_x\text{N}$ in the wide band-gap diluted magnetic semiconductor. <i>Physical Review B</i> , 2004, 70, .	3.2	18
76	Deep-level-transient spectroscopy of heavily Al-doped ZnSe layers grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2004, 96, 7332-7337.	2.5	7
77	Optical anisotropy of GaNAs grown on GaAs(001) substrate. <i>Current Applied Physics</i> , 2004, 4, 640-642.	2.4	1
78	Optical anisotropy and surface morphology of InGaAs lattice-mismatched with GaAs(001). <i>Current Applied Physics</i> , 2004, 4, 621-624.	2.4	0
79	Characterization of N-doped ZnO layers grown on (0001) GaN/ Al_2O_3 substrates by molecular beam epitaxy. <i>Current Applied Physics</i> , 2004, 4, 625-629.	2.4	12
80	Surface structure of $\text{InGaAs}/\text{InP}(001)$ ordered alloy during and after growth. <i>Applied Surface Science</i> , 2004, 237, 230-234.	6.1	7
81	Optimization of ZnSe growth on miscut GaAs substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2003, 249, 128-143.	1.5	23
82	MBE growth and characterization of A-site deficient, low-field magnetoresistance $(\text{Pr}_{1-x}\text{Sr}_x)\text{MnO}_3$ oriented thin films. <i>Journal of Crystal Growth</i> , 2003, 251, 619-622.	1.5	1
83	Characteristics of deep levels in Al-doped ZnSe grown by molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2003, 6, 567-571.	4.0	6
84	High-energy photoemission spectroscopy of ferromagnetic $\text{Ga}_{1-x}\text{Mn}_x\text{N}$. <i>Materials Science in Semiconductor Processing</i> , 2003, 6, 503-506.	4.0	6
85	Growth and characterization of $\text{Ga}_{1-x}\text{Cr}_x\text{N}$ with high Cr content grown on ZnO templates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2869-2873.	0.8	15
86	Measurements of a component of the piezo-optic tensor of Si by reflectance difference spectroscopy. <i>Journal of Applied Physics</i> , 2003, 94, 1458-1460.	2.5	2
87	Realization of one-chip-multiple-wavelength laser diodes with $\text{II}/\text{VI}/\text{III}/\text{V}$ compound semiconductors. <i>Applied Physics Letters</i> , 2003, 82, 4095-4097.	3.3	3
88	Determination of carrier concentration in n-ZnSe by reflectance difference spectroscopy: Experimental results and model calculation. <i>Journal of Applied Physics</i> , 2002, 92, 139-143.	2.5	6
89	Formation processes of CdTe quantum dots on ZnTe substrates studied by reflection high-energy electron diffraction and photoluminescence. <i>Journal of Applied Physics</i> , 2002, 92, 5490-5493.	2.5	7
90	Atomic structure of the $\text{GaAs}(001)(2\times 4)$ surface under As flux. <i>Physical Review B</i> , 2002, 65, .	3.2	60

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91	Correlation of surface chemistry of GaAs substrates with growth mode and stacking fault density in ZnSe epilayers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2002, 20, 1948.	2.1	2
92	Control of crystal polarity in a wurtzite crystal: ZnO films grown by plasma-assisted molecular-beam epitaxy on GaN. <i>Physical Review B</i> , 2002, 65, .	3.2	100
93	Molecular Beam Epitaxy of Al Doped n-ZnSe. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 381-384.	1.5	14
94	Measurements of the Linear Electro-Optic Coefficients of ZnTe by RDS. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 605-609.	1.5	1
95	ZnTe-Based Light-Emitting-Diodes Grown on ZnTe Substrates by Molecular Beam Epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 229, 995-999.	1.5	37
96	X-ray diffraction characterization of MBE grown $\text{Pr}_{1-x}\text{Sr}_x\text{MnO}_3$ thin films on $\text{NGO}(1\ 1\ 0)$. <i>Applied Surface Science</i> , 2002, 190, 408-415.	6.1	6
97	Control of polarity of heteroepitaxial ZnO films by interface engineering. <i>Applied Surface Science</i> , 2002, 190, 491-497.	6.1	21
98	Improvement in crystallinity of ZnSe by inserting a low-temperature buffer layer between the ZnSe epilayer and the GaAs substrate. <i>Journal of Crystal Growth</i> , 2002, 242, 95-103.	1.5	20
99	Surface structures of $\text{GaAs}\{111\}\text{A}$, $\sqrt{2}\times\sqrt{2}$. <i>Physical Review B</i> , 2001, 64, .	3.2	81
100	Effect of lattice mismatch on surface morphology of InAs quantum dots on (100) $\text{In}_{1-x}\text{Al}_x\text{As}/\text{InP}$. <i>Applied Physics Letters</i> , 2001, 79, 4331-4333.	3.3	13
101	Band alignment at a ZnO/GaN (0001) heterointerface. <i>Applied Physics Letters</i> , 2001, 78, 3349-3351.	3.3	125
102	Low stacking-fault density in ZnSe epilayers directly grown on epi-ready GaAs substrates without GaAs buffer layers. <i>Applied Physics Letters</i> , 2001, 78, 165-167.	3.3	55
103	Strain Relaxation of Self-Assembled InAs/GaAs(001) Quantum Dots Observed by Reflection High-Energy Electron Diffraction. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 1878-1881.	1.5	16
104	Anisotropic shape of self-assembled InAs quantum dots: Refraction effect on spot shape of reflection high-energy electron diffraction. <i>Physical Review B</i> , 2001, 64, .	3.2	50
105	Structural characteristic and magnetic properties of Mn oxide films grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2001, 227-228, 955-959.	1.5	18
106	Growth of PrSrMnO_3 -like thin films on $\text{NGO}(110)$ substrates by plasma assisted MBE. <i>Journal of Crystal Growth</i> , 2001, 227-228, 960-965.	1.5	2
107	ZnO epilayers on GaN templates: Polarity control and valence-band offset. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1429.	1.6	28
108	Structural characteristics and magnetic properties of LaMnO_2 films grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2001, 90, 351-354.	2.5	23

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109	Evolution of initial layers of plasma-assisted MBE grown ZnO on (0001)GaN/sapphire. Journal of Crystal Growth, 2000, 214-215, 81-86.	1.5	30
110	In situ measurement of carrier concentration in n-ZnSe by reflectance difference spectroscopy (RDS). Journal of Crystal Growth, 2000, 214-215, 547-551.	1.5	6
111	Self-organized formation processes of CdSe quantum dots studied by reflection high-energy electron diffraction. Journal of Crystal Growth, 2000, 214-215, 703-706.	1.5	8
112	Growth of GaN single crystals from a Na-Ga melt at 750°C and 5MPa of N ₂ . Journal of Crystal Growth, 2000, 218, 7-12.	1.5	68
113	Surface reconstruction and crystal structure of MgSe films grown on ZnTe substrates by MBE. Journal of Crystal Growth, 2000, 208, 253-258.	1.5	15
114	Effects of a low-temperature buffer layer on structural properties of ZnO epilayers grown on (111)CaF ₂ by two-step MBE. Journal of Crystal Growth, 2000, 208, 389-394.	1.5	20
115	Control and characterization of ZnO/GaN heterointerfaces in plasma-assisted MBE-grown ZnO films on GaN/Al ₂ O ₃ . Applied Surface Science, 2000, 159-160, 441-448.	6.1	30
116	Adsorption processes of Se on the GaAs(111)A(2x2) surface. Applied Surface Science, 2000, 162-163, 419-424.	6.1	2
117	Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates. Applied Physics Letters, 2000, 77, 3571-3573.	3.3	63
118	Observation of bulk Bragg-reflection using reflection high-energy electron diffraction on Mn ₃ O ₄ -like films grown on MgO (001) by molecular beam epitaxy. Surface Science, 2000, 445, 151-158.	1.9	7
119	Structure and composition of the ZnSe(001) surface during atomic-layer epitaxy. Physical Review B, 1999, 60, 8326-8332.	3.2	35
120	In situ observation of strain-induced optical anisotropy of Zn _{1-x} Se _x /GaAs(110) during molecular-beam epitaxy. Physical Review B, 1999, 60, 8909-8914.	3.2	8
121	Real-time analysis of adsorption processes of Zn on the GaAs(001)A(2x4) surface. Physical Review B, 1999, 60, 8713-8718.	3.2	18
122	Adsorption of Zn on the GaAs(001)-(2x4) surface. Applied Physics Letters, 1999, 74, 2975-2977.	3.3	10
123	Self-assembled formation of ZnCdSe quantum dots on atomically smooth ZnSe surfaces on GaAs(001) by molecular beam epitaxy. Thin Solid Films, 1999, 357, 1-7.	1.8	11
124	Atomic layer epitaxy processes of ZnSe on GaAs(001) as observed by beam-rocking reflection high-energy electron diffraction (RHEED) and total-reflection-angle X-ray spectroscopy (TRAXS). Journal of Crystal Growth, 1999, 201-202, 490-493.	1.5	7
125	Two-step MBE growth of ZnO layers on electron beam exposed (111)CaF ₂ . Journal of Crystal Growth, 1999, 207, 87-94.	1.5	37
126	Structure of Se-adsorbed GaAs(111)A-(2x3)-R30° surface. Physical Review B, 1999, 59, 8032-8036.	3.2	17

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127	Scanning tunneling microscopy study of the initial reaction of SiH ₂ Cl ₂ molecules with the Si(111)-7 \times 7 surface. Applied Surface Science, 1998, 130-132, 23-28.	6.1	4
128	Properties of self-organized CdSe quantum dots on an atomically flat (111)A ZnSe surface. Applied Surface Science, 1998, 130-132, 755-759.	6.1	2
129	Electron Standing Wave at a Surface during Reflection High Energy Electron Diffraction and Adatom Height Determination. Physical Review Letters, 1995, 75, 669-672.	7.8	13
130	Rocking-curve analysis of reflection high-energy electron diffraction from the Si(111)-($\sqrt{3} \times \sqrt{3}$)R30 $^\circ$ -Al, -Ga, and -In surfaces. Physical Review B, 1995, 51, 13320-13325.	3.2	72
131	Atomic layer control in Sr ϵ artificial lattice growth. Applied Physics Letters, 1994, 65, 1717-1719.	3.3	22
132	Surface reactions at the controlled structure of SrTiO ₃ (001). Surface and Interface Analysis, 1994, 22, 412-416.	1.8	31
133	Layer controlled growth of oxide superconductors. Applied Surface Science, 1994, 82-83, 487-493.	6.1	17
134	Study of the Si(111)7 \times 7 surface by RHEED rocking curve analysis. Surface Science, 1994, 313, 143-154.	1.9	53
135	Structure and electronic state of the TiO ₂ and SrO terminated SrTiO ₃ (100) surfaces. Surface Science, 1993, 287-288, 377-381.	1.9	140
136	Surface structure of SrTiO ₃ (001) with various surface treatments. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 2649-2654.	2.1	48
137	Atomic Layer Growth of SrCuO ₂ Thin Film by Molecular Beam Epitaxy.. Hyomen Kagaku, 1993, 14, 283-287.	0.0	1
138	Glancing Angle Dependence of the X-Ray Emission Measured under Total Reflection Angle X-Ray Spectroscopy (TRAXS) Condition during Reflection High Energy Electron Diffraction Observation. Japanese Journal of Applied Physics, 1992, 31, L1503-L1505.	1.5	13
139	Molecular beam epitaxial growth of superconducting Ba ₂ DyCu ₃ O _{6.5} thin films at 420 ϵ C using NO ₂ as an oxidant. Applied Physics Letters, 1992, 61, 1971-1973.	3.3	14
140	Reaction between copper dipivaloylmethanate Cu(DPM) ₂ and H ₂ O adsorbed on SrTiO ₃ (100). Surface Science, 1992, 262, L139-L143.	1.9	8
141	Study of successive phase transitions of the Si(001)-Bi surface by RHEED. Surface Science, 1991, 242, 137-142.	1.9	44
142	The reaction of copper and calcium dipivaloylmethanates (Cu(DPM) ₂ and Ca(DPM) ₂) with hydroxyls on oxide surface. Surface Science, 1991, 242, 508-512.	1.9	23
143	In situ RHEED and XPS studies on ceramic layer epitaxy in UHV system. AIP Conference Proceedings, 1991, , ,	0.4	0
144	Ultra thin film of Bi cuprate grown by a low temperature molecular beam epitaxy. Physica C: Superconductivity and Its Applications, 1991, 185-189, 2057-2058.	1.2	0

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145	Molecular beam epitaxy of Bi ₂ Sr ₂ CuO _x and Bi ₂ Sr ₂ Ca _{0.85} Sr _{0.15} Cu ₂ O _x ultra thin films at 300°C. Journal of Crystal Growth, 1991, 112, 745-752.	1.5	58
146	Structure and growth mechanism of ultrathin films of Bi cuprates grown by low-temperature MBE. Physica C: Superconductivity and Its Applications, 1991, 190, 27-30.	1.2	5
147	Selective surface reaction between metal compounds and surface functional groups. Physica C: Superconductivity and Its Applications, 1991, 190, 148-150.	1.2	1
148	Surface structure and oxidation of Si(001)Bi. Vacuum, 1990, 41, 650-651.	3.5	17
149	Molecular Beam Epitaxy Study of Bi ₂ Sr ₂ CuO _x Using NO ₂ as an Oxidizing Agent. Japanese Journal of Applied Physics, 1990, 29, L1111-L1113.	1.5	49
150	Ultrathin film of Bi ₂ Sr ₂ CuO _x formed by molecular beam epitaxy using NO ₂ . Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 4104-4105.	2.1	13
151	Study of surface structure by kinetic-energy dependence of polar-angle photoelectron diffraction. Surface Science, 1989, 221, 244-252.	1.9	17
152	Study on the Elementary Steps of the Epitaxial Growth of Bi-Sr-Ca-Cu-O on the Surface of Si and MgO by Means of Rheed and Photoelectron Spectroscopies. Materials Research Society Symposia Proceedings, 1989, 169, 715.	0.1	0
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